

FIG.1

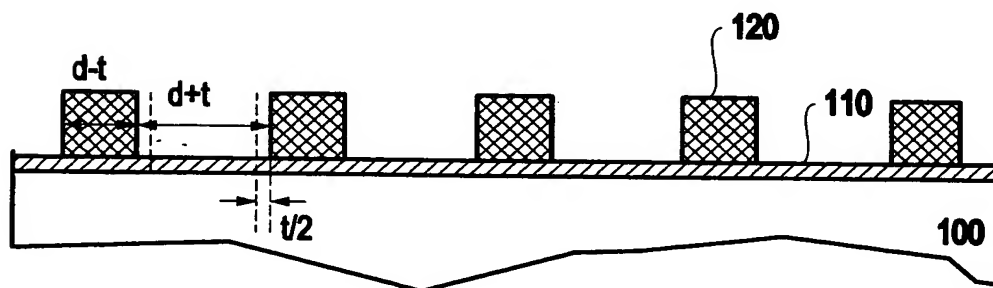


FIG.2

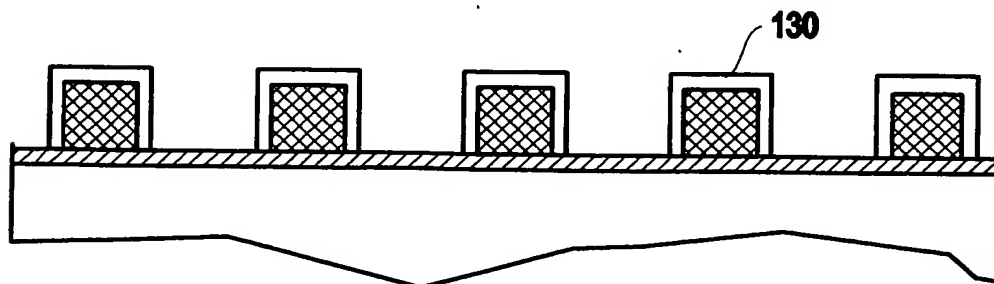


FIG.3

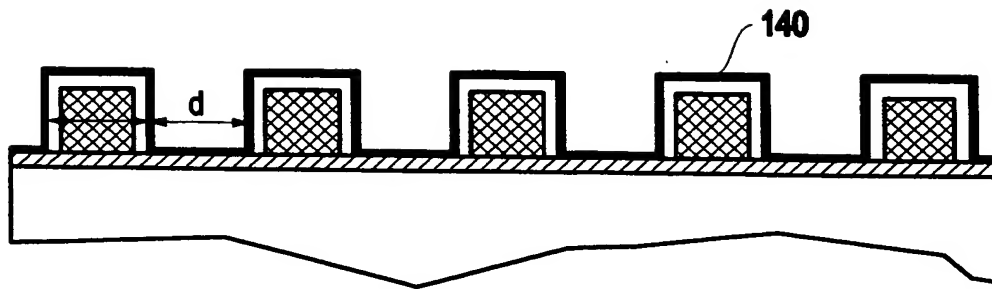


FIG. 4

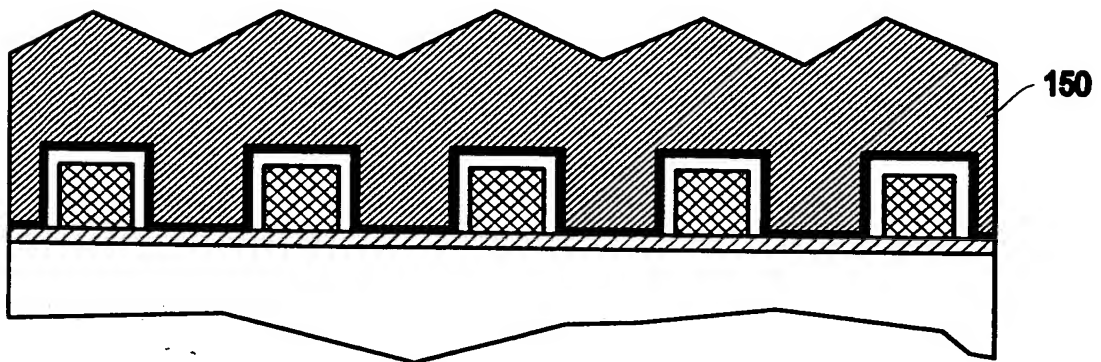


FIG. 5

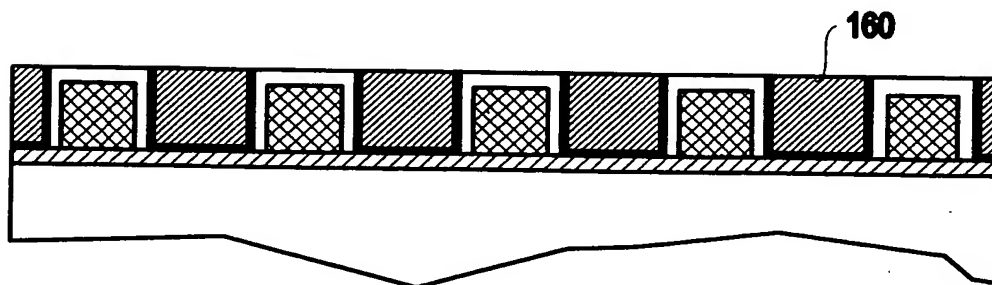


FIG. 6

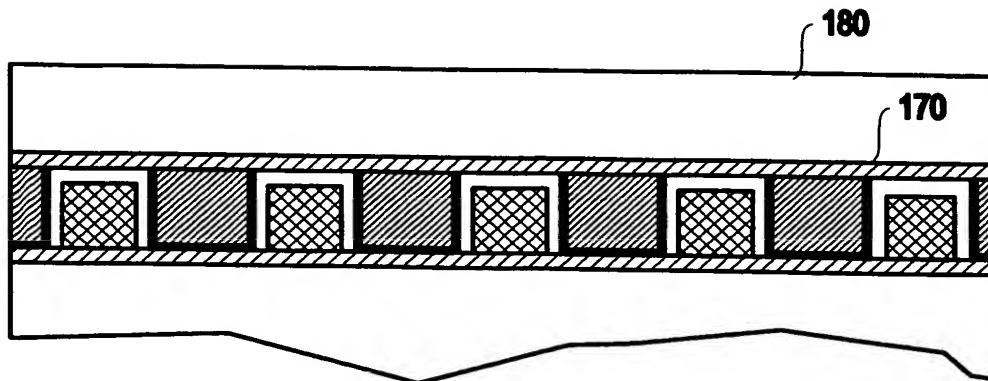


FIG.7

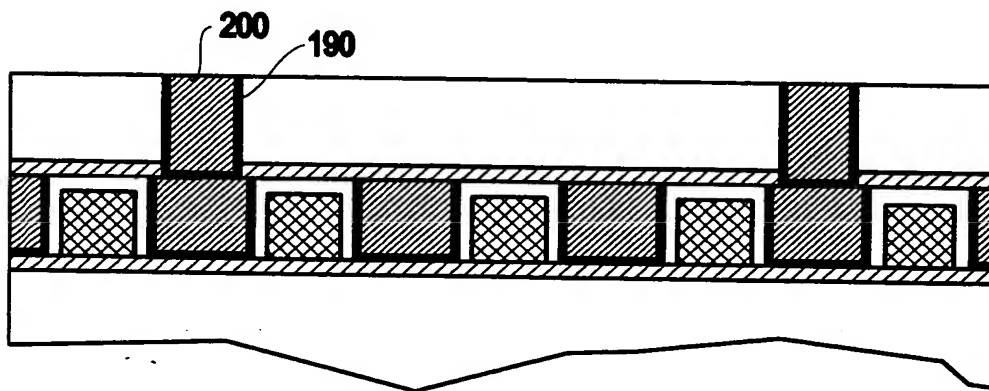


FIG.8

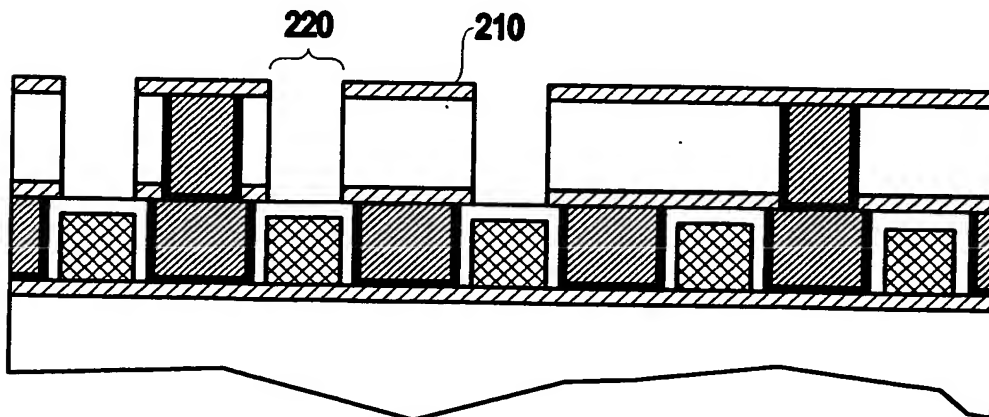


FIG.9

Figure 1 is a cross-sectional view of a semiconductor device. The top part shows a cross-section with various layers and structures. The bottom part shows a plan view of the device with regions labeled 250 through 259. Regions 250, 252, 254, 256, 258, and 259 are shaded with different patterns. Regions 251, 253, 255, 257, and 259 are unshaded. Regions 250, 252, 254, 256, and 258 are labeled Vs1, Vs2, Vs3, Vp1, and Vp2 respectively. Regions 257 and 259 are labeled gnd. A dashed line indicates the cross-section line X-X'.

FIG.11

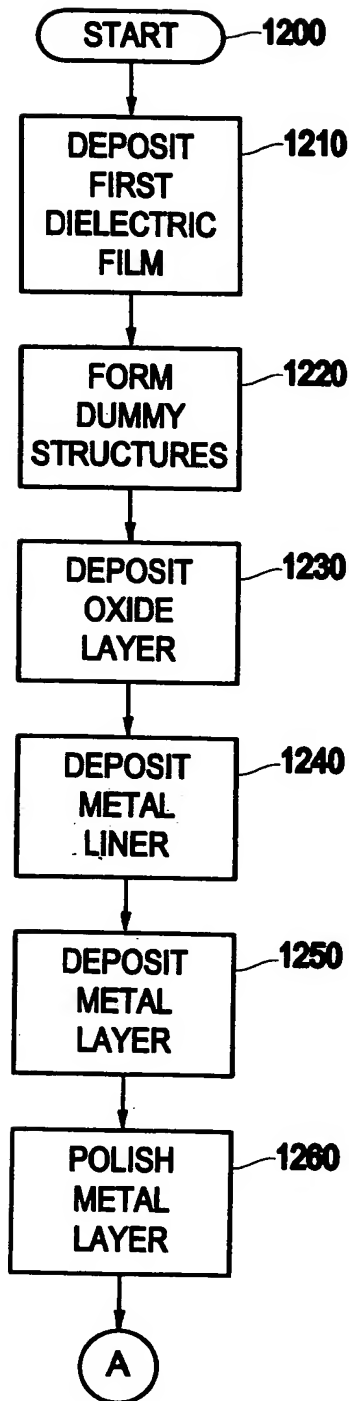


FIG. 12A

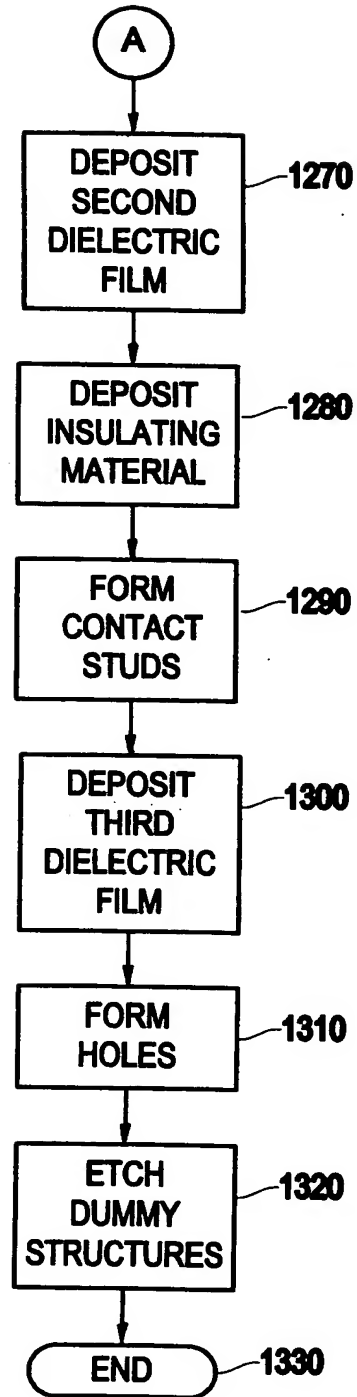


FIG. 12B

6/9
YOR920010692US1

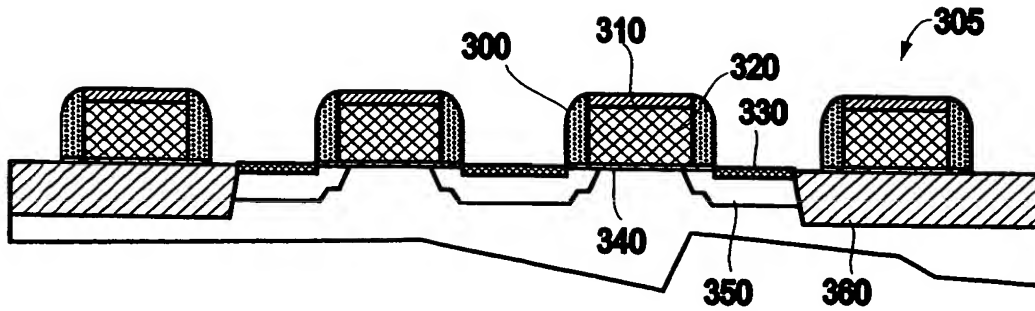


FIG. 13

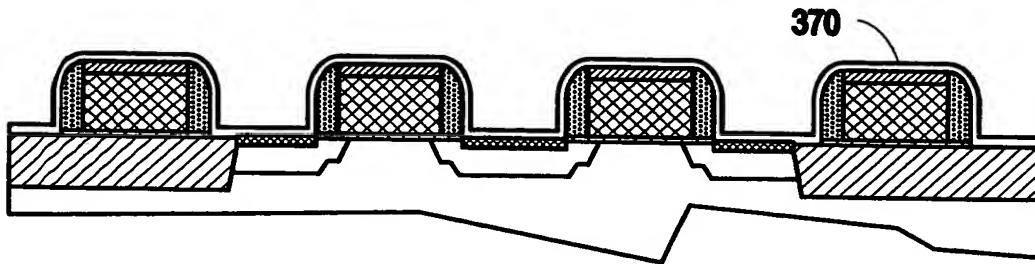


FIG. 14

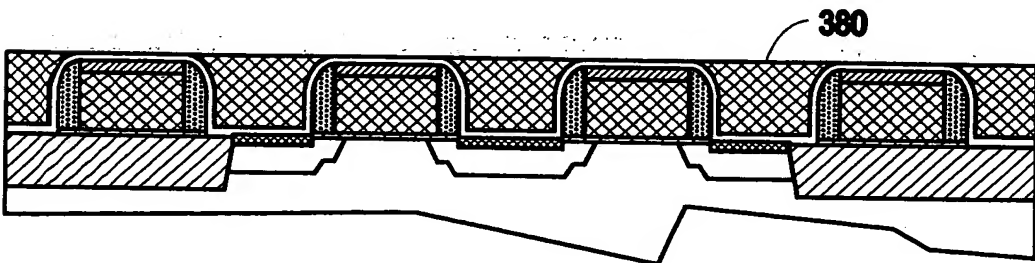


FIG. 15

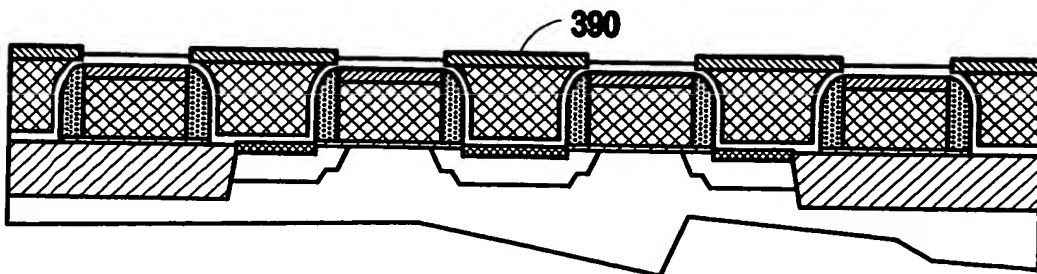


FIG. 16

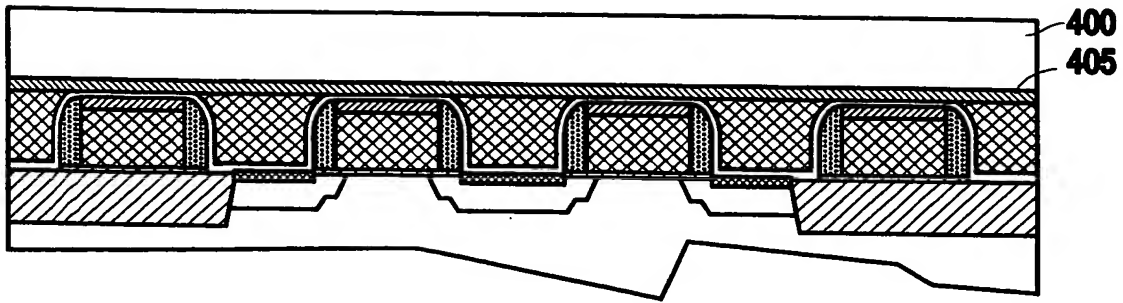


FIG. 17

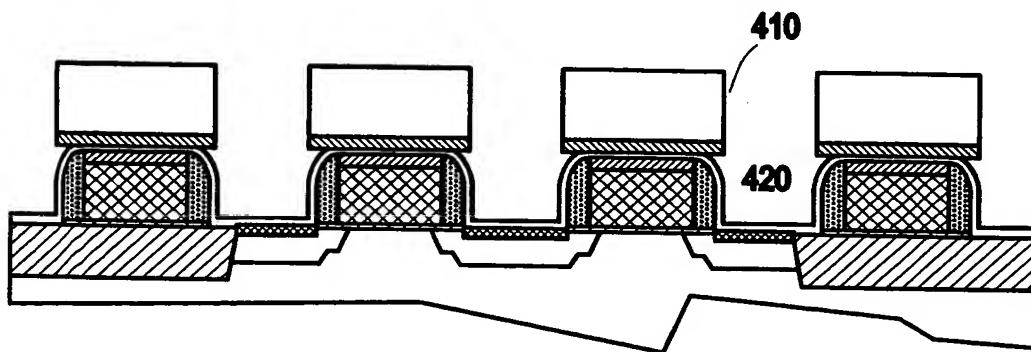


FIG. 18

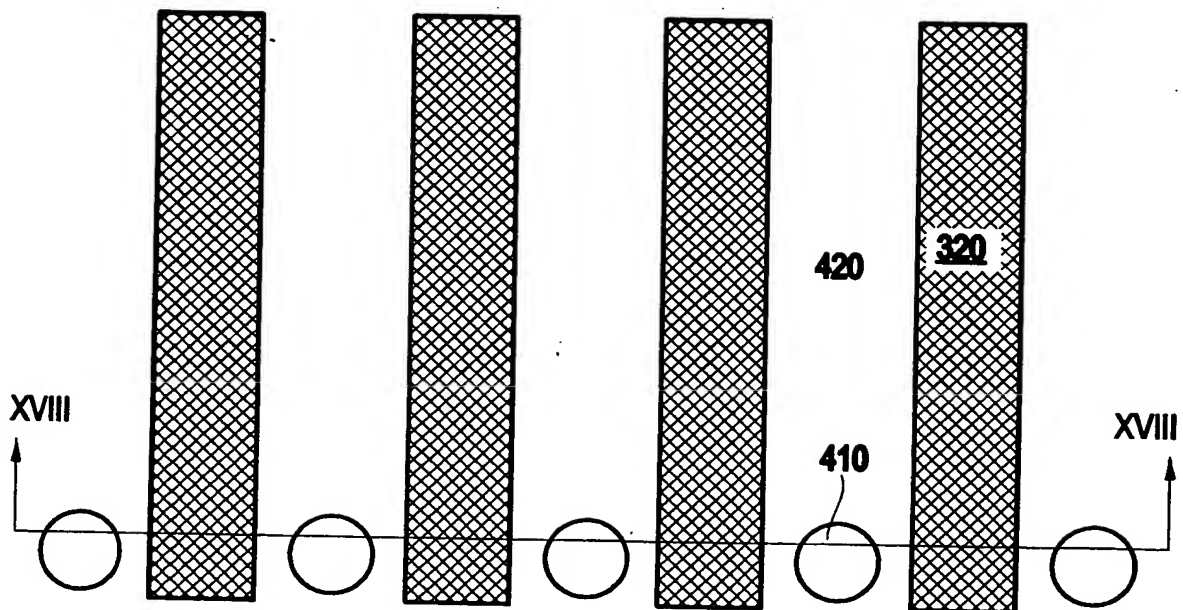


FIG. 19

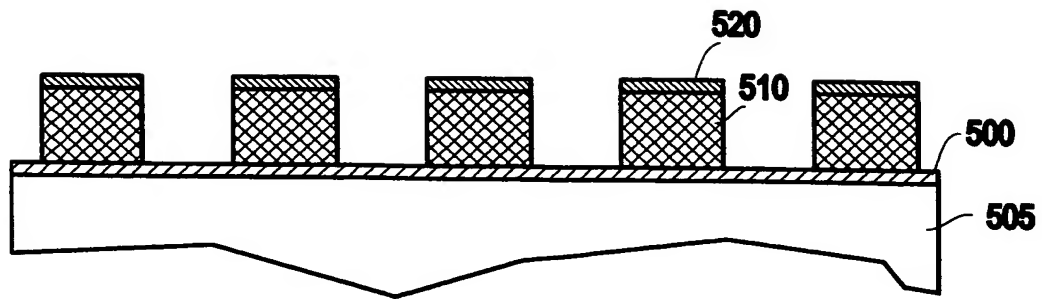


FIG.20

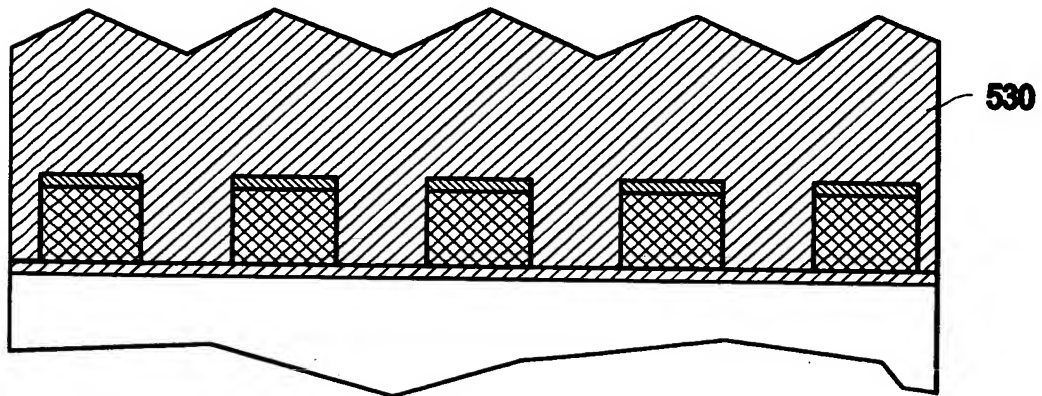


FIG.21

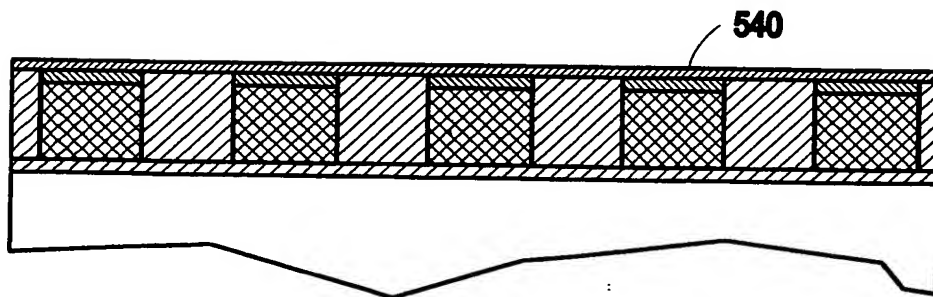


FIG.22

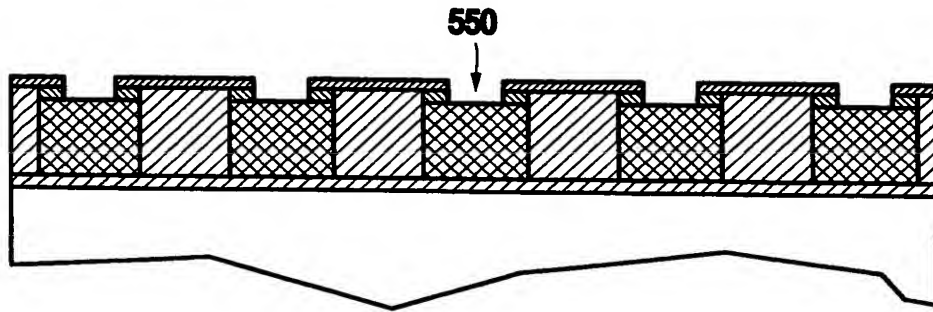


FIG.23

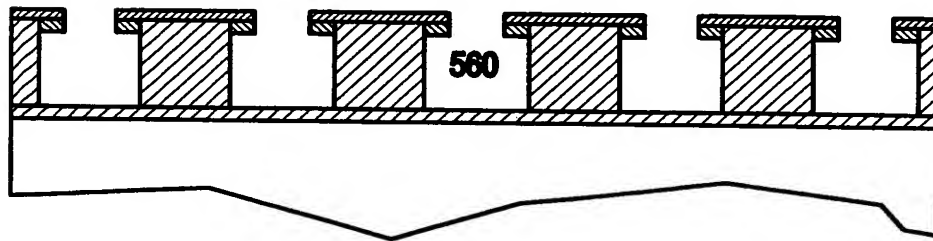


FIG.24

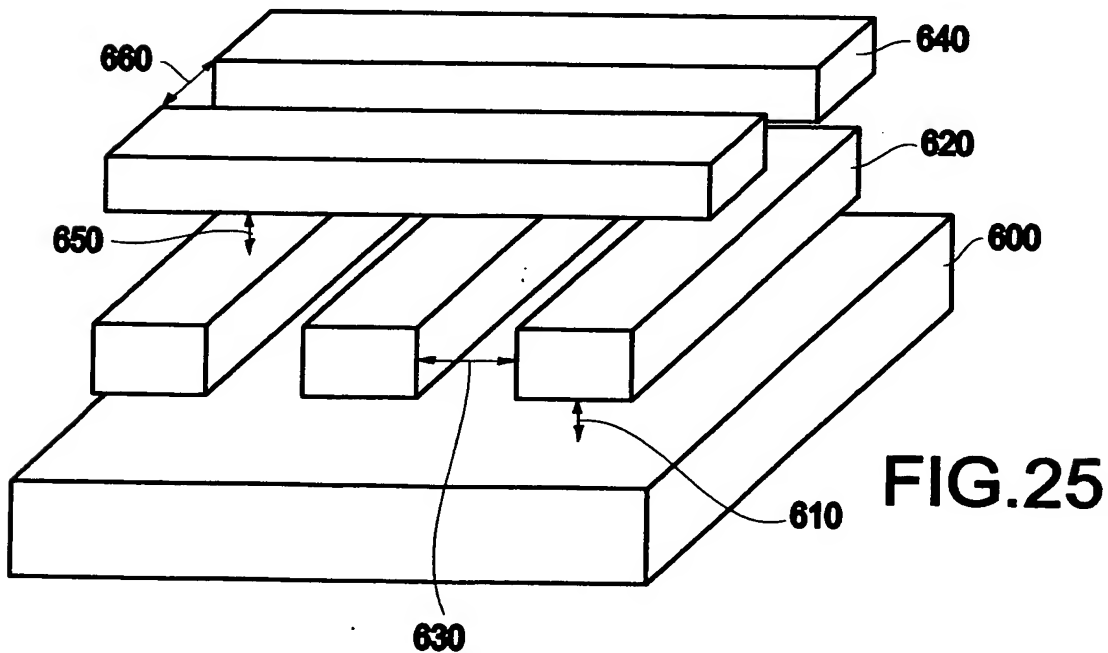


FIG.25